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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, POR, PWM, WDT
Number of I/O	54
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope, 16x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4147axi-s475

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Watch Crystal Oscillator (WCO)

The PSoC 4100S Plus clock subsystem also implements a low-frequency (32-kHz watch crystal) oscillator that can be used for precision timing applications.

External Crystal Oscillators (ECO)

The PSoC 4100S Plus also implements a 4 to 33 MHz crystal oscillator.

Watchdog Timer and Counters

A watchdog timer is implemented in the clock block running from the ILO; this allows watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the set timeout occurs. The watchdog reset is recorded in a Reset Cause register, which is firmware readable. The Watchdog counters can be used to implement a Real-Time clock using the 32-kHz WCO.

Reset

PSoC 4100S Plus can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through reset and allows software to determine the cause of the reset. An XRES pin is reserved for external reset by asserting it active low. The XRES pin has an internal pull-up resistor that is always enabled.

Analog Blocks

12-bit SAR ADC

The 12-bit, 1-Msps SAR ADC can operate at a maximum clock rate of 18 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

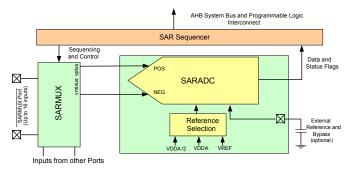
The Sample-and-Hold (S/H) aperture is programmable allowing the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. It is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer. The sequencer cycles through selected channels autonomously (sequencer scan) with zero switching overhead (that is, aggregate sampling bandwidth is equal to 1 Msps whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware driven switching. A feature provided by the sequencer is buffering of each channel to reduce CPU interrupt service requirements. To accommodate signals with varying source impedance and frequency, it is possible to have different sample times programmable for each channel. Also, signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range

values without the necessity of having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is not available in Deep Sleep mode as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 V to 5.5 V.

Figure 4. SAR ADC



Two Opamps (Continuous-Time Block; CTB)

PSoC 4100S Plus has two opamps with Comparator modes which allow most common analog functions to be performed on-chip eliminating external components; PGAs, Voltage Buffers, Filters, Trans-Impedance Amplifiers, and other functions can be realized, in some cases with external passives. saving power, cost, and space. The on-chip opamps are designed with enough bandwidth to drive the Sample-and-Hold circuit of the ADC without requiring external buffering.

Low-power Comparators (LPC)

PSoC 4100S Plus has a pair of low-power comparators, which can also operate in Deep Sleep modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid metastability unless operating in an asynchronous power mode where the system wake-up circuit is activated by a comparator switch event. The LPC outputs can be routed to pins.

Current DACs

PSoC 4100S Plus has two IDACs, which can drive any of the pins on the chip. These IDACs have programmable current ranges.

Analog Multiplexed Buses

PSoC 4100S Plus has two concentric independent buses that go around the periphery of the chip. These buses (called amux buses) are connected to firmware-programmable analog switches that allow the chip's internal resources (IDACs, comparator) to connect to any pin on the I/O Ports.



Programmable Digital Blocks

Smart I/O Block

The Smart I/O block is a fabric of switches and LUTs that allows Boolean functions to be performed in signals being routed to the pins of a GPIO port. The Smart I/O can perform logical operations on input pins to the chip and on signals going out as outputs.

Fixed Function Digital Blocks

Timer/Counter/PWM (TCPWM) Block

The TCPWM block consists of a 16-bit counter with user-programmable period length. There is a capture register to record the count value at the time of an event (which may be an I/O event), a period register that is used to either stop or auto-reload the counter when its count is equal to the period register, and compare registers to generate compare value signals that are used as PWM duty cycle outputs. The block also provides true and complementary outputs with programmable offset between them to allow use as dead-band programmable complementary PWM outputs. It also has a Kill input to force outputs to a predetermined state; for example, this is used in motor drive systems when an over-current state is indicated and the PWM driving the FETs needs to be shut off immediately with no time for software intervention. Each block also incorporates a Quadrature decoder. There are eight TCPWM blocks in PSoC 4100S Plus.

Serial Communication Block (SCB)

PSoC 4100S Plus has five serial communication blocks, which can be programmed to have SPI, 1^{2} C, or UART functionality.

I²C Mode: The hardware I²C block implements a full multi-master and slave interface (it is capable of multi-master arbitration). This block is capable of operating at speeds of up to 400 kbps (Fast Mode) and has flexible buffering options to reduce interrupt overhead and latency for the CPU. It also supports EZI2C that creates a mailbox address range in the memory of PSoC 4100S Plus and effectively reduces I²C communication to reading from and writing to an array in memory. In addition, the block supports an 8-deep FIFO for receive and transmit which, by increasing the time given for the CPU to read data, greatly reduces the need for clock stretching caused by the CPU not having read data on time.

The I²C peripheral is compatible with the I²C Standard-mode and Fast-mode devices as defined in the NXP I²C-bus specification and user manual (UM10204). The I²C bus I/O is implemented with GPIO in open-drain modes.

PSoC 4100S Plus is not completely compliant with the I²C spec in the following respect:

GPIO cells are not overvoltage tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I²C system. **UART Mode**: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated.

SPI Mode: The SPI mode supports full Motorola SPI, TI SSP (adds a start pulse used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO.

CAN

There is a CAN 2.0B block with support for TT-CAN.

GPIO

PSoC 4100S Plus has up to 54 GPIOs. The GPIO block implements the following:

- Eight drive modes:
- □ Analog input mode (input and output buffers disabled)
- Input only
- Weak pull-up with strong pull-down
- Strong pull-up with weak pull-down
- Open drain with strong pull-down
- Open drain with strong pull-up
- □ Strong pull-up with strong pull-down
- Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes
- Selectable slew rates for dV/dt related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width (less for Ports 5 and 6). During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it.



Special Function Peripherals

CapSense

CapSense is supported in the PSoC 4100S Plus through a CapSense Sigma-Delta (CSD) block that can be connected to any pins through an analog multiplex bus via analog switches. CapSense function can thus be provided on any available pin or group of pins in a system under software control. A PSoC Creator component is provided for the CapSense block to make it easy for the user.

Shield voltage can be driven on another analog multiplex bus to provide water-tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input. Proximity sensing can also be implemented.

The CapSense block has two IDACs, which can be used for general purposes if CapSense is not being used (both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available).

The CapSense block also provides a 10-bit Slope ADC function which can be used in conjunction with the CapSense function.

The CapSense block is an advanced, low-noise, programmable block with programmable voltage references and current source ranges for improved sensitivity and flexibility. It can also use an external reference voltage. It has a full-wave CSD mode that alternates sensing to VDDA and ground to null out power-supply related noise.

LCD Segment Drive

PSoC 4100S Plus has an LCD controller, which can drive up to 4 commons and up to 50 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as Digital Correlation and PWM. Digital Correlation pertains to modulating the frequency and drive levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal to zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays. PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; one 32-bit register per port).



Pinouts

The following table provides the pin list for PSoC 4100S Plus for the 44-pin TQFP and 64-pin TQFP Normal and Fine Pitch packages.

	64-TQFP		44-TQFP
Pin	Name	Pin	Name
39	P0.0	24	P0.0
40	P0.1	25	P0.1
41	P0.2	26	P0.2
42	P0.3	27	P0.3
43	P0.4	28	P0.4
44	P0.5	29	P0.5
45	P0.6	30	P0.6
46	P0.7	31	P0.7
47	XRES	32	XRES
48	VCCD	33	VCCD
49	VSSD		
50	VDDD	34	VDDD
51	P5.0		
52	P5.1		
53	P5.2		
54	P5.3		
55	P5.5		
56	VDDA	35	VDDA
57	VSSA	36	VSSA
58	P1.0	37	P1.0
59	P1.1	38	P1.1
60	P1.2	39	P1.2
61	P1.3	40	P1.3
62	P1.4	41	P1.4
63	P1.5	42	P1.5
64	P1.6	43	P1.6
1	P1.7	44	P1.7
		1	VSSD
2	P2.0	2	P2.0
3	P2.1	3	P2.1
4	P2.2	4	P2.2
5	P2.3	5	P2.3
6	P2.4	6	P2.4
7	P2.5	7	P2.5
8	P2.6	8	P2.6
9	P2.7	9	P2.7
10	VSSD	10	P6.0
11	No Connect (NC)		
12	P6.0		
13	P6.1		



	64-TQFP	44-TQFP				
Pin	Name	Pin	Name			
14	P6.2					
15	P6.4					
16	P6.5					
17	VSSD					
17	VSSD					
18	P3.0	11	P3.0			
19	P3.1	12	P3.1			
20	P3.2	13	P3.2			
21	P3.3	14	P3.3			
22	P3.4	15	P3.4			
23	P3.5	16	P3.5			
24	P3.6	17	P3.6			
25	P3.7	18	P3.7			
26	VDDD	19	VDDD			
27	P4.0	20	P4.0			
28	P4.1	21	P4.1			
29	P4.2	22	P4.2			
30	P4.3	23	P4.3			
31	P4.4					
32	P4.5					
33	P4.6					
34	P4.7					
35	P5.6					
36	P5.7					
37	P7.0					
38	P7.1					

Descriptions of the Power pins are as follows:

VDDD: Power supply for the digital section.

VDDA: Power supply for the analog section.

VSSD, VSSA: Ground pins for the digital and analog sections respectively.

VCCD: Regulated digital supply (1.8 V ±5%)

VDD: Power supply to all sections of the chip

VSS: Ground for all sections of the chip

GPIOs by package:

	64 TQFP	44 TQFP		
Number	54	37		



Table 2. DC Specifications (continued)

Typical values measured at V_DD = 3.3 V and 25 $^\circ\text{C}.$

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
Sleep Mode, V	DDD = 1.8 V to	5.5 V (Regulator on)					
SID22	I _{DD17}	I ² C wakeup WDT, and Comparators on	-	1.1	1.8	mA	6 MHZ. Max is at 85 °C and 5.5 V
SID25	I _{DD20}	I ² C wakeup, WDT, and Comparators on	-	1.5	2.1	-	12 MHZ. Max is at 85 °C and 5.5 V
Sleep Mode, V	_{DDD} = 1.71 V to	1.89 V (Regulator bypassed)					
SID28	I _{DD23}	I ² C wakeup, WDT, and Comparators on	-	1.1	1.8	mA	6 MHZ. Max is at 85 °C and 1.89 V
SID28A	I _{DD23A}	I ² C wakeup, WDT, and Comparators on	_	1.5	2.1	mA	12 MHZ. Max is at 85 °C and 1.89 V
Deep Sleep Me	ode, V _{DD} = 1.8 V	/ to 3.6 V (Regulator on)					
SID30	I _{DD25}	I^2C wakeup and WDT on; T = -40 °C to 60 °C	-	2.5	40	μA	T = -40 °C to 60 °C
SID31	I _{DD26}	I ² C wakeup and WDT on	_	2.5	125	μA	Max is at 3.6 V and 85 °C
Deep Sleep Me	ode, V _{DD} = 3.6 V	/ to 5.5 V (Regulator on)					
SID33	I _{DD28}	I^2C wakeup and WDT on; T = -40 °C to 60 °C	_	2.5	40	μA	T = -40 °C to 60 °C
SID34	I _{DD29}	I ² C wakeup and WDT on	_	2.5	125	μA	Max is at 5.5 V and 85 °C
Deep Sleep Me	ode, V _{DD} = V _{CC}	_D = 1.71 V to 1.89 V (Regulator bypasse	d)				
SID36	I _{DD31}	I^2C wakeup and WDT on; T = -40 °C to 60 °C	_	2.5	60	μA	T = -40 °C to 60 °C
SID37	I _{DD32}	I ² C wakeup and WDT on	_	2.5	180	μA	Max is at 1.89 V and 85 °C
XRES Current	•	· · · · · ·		•	•	•	•
SID307	I _{DD_XR}	Supply current while XRES asserted	_	2	5	mA	-

Table 3. AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID48	F _{CPU}	CPU frequency	DC	-	48	MHz	$1.71 \leq V_{DD} \leq 5.5$
SID49 ^[2]	T _{SLEEP}	Wakeup from Sleep mode	-	0	_	us	
SID50 ^[2]	T _{DEEPSLEEP}	Wakeup from Deep Sleep mode	-	35	_	μο	



GPIO

Table 4. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID57	V _{IH} ^[3]	Input voltage high threshold	$0.7\times V_{DDD}$	-	-		CMOS Input
SID58	V _{IL}	Input voltage low threshold	-	_	$0.3 \times V_{DDD}$		CMOS Input
SID241	V _{IH} ^[3]	LVTTL input, V _{DDD} < 2.7 V	$0.7\times V_{DDD}$	-	-		_
SID242	V _{IL}	LVTTL input, V _{DDD} < 2.7 V	-	_	$0.3 \times V_{DDD}$		_
SID243	V _{IH} ^[3]	LVTTL input, $V_{DDD} \ge 2.7 V$	2.0	-	_		_
SID244	V _{IL}	LVTTL input, $V_{DDD} \ge 2.7 V$	_	-	0.8	V	_
SID59	V _{OH}	Output voltage high level	V _{DDD} -0.6	-	-		I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V _{OH}	Output voltage high level	V _{DDD} -0.5	-	-		I _{OH} = 1 mA at 1.8 V V _{DDD}
SID61	V _{OL}	Output voltage low level	-	-	0.6		I _{OL} = 4 mA at 1.8 V V _{DDD}
SID62	V _{OL}	Output voltage low level	-	-	0.6		I_{OL} = 10 mA at 3 V V _{DDD}
SID62A	V _{OL}	Output voltage low level	-	-	0.4		I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	-
SID64	R _{PULLDOWN}	Pull-down resistor	3.5	5.6	8.5	N22	_
SID65	I _{IL}	Input leakage current (absolute value)	-	_	2	nA	25 °C, V _{DDD} = 3.0 V
SID66	C _{IN}	Input capacitance	-	-	7	pF	-
SID67 ^[4]	V _{HYSTTL}	Input hysteresis LVTTL	25	40	-		$V_{DDD} \ge 2.7 V$
SID68 ^[4]	V _{HYSCMOS}	Input hysteresis CMOS	0.05 × V _{DDD}	-	-	mV	V _{DD} < 4.5 V
SID68A ^[4]	V _{HYSCMOS5V5}	Input hysteresis CMOS	200	-	-		V _{DD} > 4.5 V
SID69 ^[4]	IDIODE	Current through protection diode to V_{DD}/V_{SS}	-	_	100	μA	_
SID69A ^[4]	I _{TOT_GPIO}	Maximum total source or sink chip current	-	_	200	mA	-

Table 5. GPIO AC Specifications(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID70	T _{RISEF}	Rise time in fast strong mode	2	_	12	ns	3.3 V V _{DDD} , Cload = 25 pF
SID71	T _{FALLF}	Fall time in fast strong mode	2	_	12		3.3 V V _{DDD} , Cload = 25 pF
SID72	T _{RISES}	Rise time in slow strong mode	10	-	60	_	3.3 V V _{DDD} , Cload = 25 pF

3. V_{IH} must not exceed V_{DDD} + 0.2 V.
 4. Guaranteed by characterization.



Table 5. GPIO AC Specifications (continued)

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID73	T _{FALLS}	Fall time in slow strong mode	10	-	60	-	3.3 V V _{DDD} , Cload = 25 pF
SID74	F _{GPIOUT1}	GPIO F _{OUT} ; 3.3 V \leq V _{DDD} \leq 5.5 V Fast strong mode	_	-	33		90/10%, 25 pF load, 60/40 duty cycle
SID75	F _{GPIOUT2}	GPIO F _{OUT} ; 1.71 V≤ V _{DDD} ≤ 3.3 V Fast strong mode	_	_	16.7		90/10%, 25 pF load, 60/40 duty cycle
SID76	F _{GPIOUT3}	GPIO F _{OUT} ; 3.3 V \leq V _{DDD} \leq 5.5 V Slow strong mode	_	_	7	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID245	F _{GPIOUT4}	GPIO F_{OUT} ; 1.71 V \leq V _{DDD} \leq 3.3 V Slow strong mode.	_	-	3.5		90/10%, 25 pF load, 60/40 duty cycle
SID246	F _{GPIOIN}	GPIO input operating frequency; 1.71 V \leq V _{DDD} \leq 5.5 V	_	_	48		90/10% V _{IO}

XRES

Table 6. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID77	V _{IH}	Input voltage high threshold	$0.7 \times V_{DDD}$	-	-	V	CMOS Input
SID78	V _{IL}	Input voltage low threshold	-	-	$0.3\times V_{DDD}$	V	
SID79	R _{PULLUP}	Pull-up resistor	-	60	-	kΩ	-
SID80	C _{IN}	Input capacitance	-	-	7	pF	-
SID81 ^[5]	V _{HYSXRES}	Input voltage hysteresis	-	100	-	mV	Typical hysteresis is 200 mV for V _{DD} > 4.5 V
SID82	I _{DIODE}	Current through protection diode to V_{DD}/V_{SS}	_	_	100	μA	

Table 7. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID83 ^[5]	T _{RESETWIDTH}	Reset pulse width	1	-	-	μs	-
BID194 ^[5]	TRESETWAKE	Wake-up time from reset release	-	-	2.7	ms	-



Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID283	V _{OUT_1}	power=hi, lload=10 mA	0.5	_	V _{DDA} -0.5		_
SID284	V _{OUT_2}	power=hi, lload=1 mA	0.2	_	V _{DDA} -0.2	V	_
SID285	V _{OUT_3}	power=med, lload=1 mA	0.2	-	V _{DDA} -0.2	v	-
SID286	V _{OUT_4}	power=lo, lload=0.1 mA	0.2	-	V _{DDA} -0.2		-
SID288	V _{OS_TR}	Offset voltage, trimmed	-1.0	±0.5	1.0		High mode, input 0 V to V _{DDA} -0.2 V
SID288A	V _{OS_TR}	Offset voltage, trimmed	-	±1	_	mV	Medium mode, input 0 V to V _{DDA} -0.2 V
SID288B	V _{OS_TR}	Offset voltage, trimmed	-	±2	-		Low mode, input 0 V to V _{DDA} -0.2 V
SID290	V _{OS_DR_TR}	Offset voltage drift, trimmed	-10	±3	10	μV/°C	High mode
SID290A	V _{OS_DR_TR}	Offset voltage drift, trimmed	-	±10	-		Medium mode
SID290B	V _{OS_DR_TR}	Offset voltage drift, trimmed	_	±10	-	μV/°C	Low mode
SID291	CMRR	DC	70	80	-		Input is 0 V to V_{DDA} -0.2 V, Output is 0.2 V to V_{DDA} -0.2 V
SID292	PSRR	At 1 kHz, 10-mV ripple	70	85	-	dB	V _{DDD} = 3.6 V, high-power mode, input is 0.2 V to V _{DDA} -0.2 V
	Noise						
SID294	VN2	Input-referred, 1 kHz, power = Hi	-	72	_		Input and output are at 0.2 V to V_{DDA} -0.2 V
SID295	VN3	Input-referred, 10 kHz, power = Hi	Ι	28	_	nV/rtHz	Input and output are at 0.2 V to V _{DDA} -0.2 V
SID296	VN4	Input-referred, 100 kHz, power = Hi	-	15	-		Input and output are at 0.2 V to V _{DDA} -0.2 V
SID297	C _{LOAD}	Stable up to max. load. Performance specs at 50 pF.	-	_	125	pF	_
SID298	SLEW_RATE	Cload = 50 pF, Power = High, V_{DDA} = 2.7 V	6	-	-	V/µs	-
SID299	T_OP_WAKE	From disable to enable, no external RC dominating	-	-	25	μs	_
SID299A	OL_GAIN	Open Loop Gain	-	90	-	dB	
	COMP_MODE	Comparator mode; 50 mV drive, T _{rise} =T _{fall} (approx.)					

Table 8. CTBm Opamp Specifications (continued)



Temperature Sensor

Table 11. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details / Conditions
SID93	TSENSACC	Temperature sensor accuracy	-5	±1	5	°C	–40 to +85 °C

SAR ADC

Table 12. SAR ADC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SAR ADC	DC Specification	ons					
SID94	A_RES	Resolution	-	-	12	bits	
SID95	A_CHNLS_S	Number of channels - single ended	-	-	16		
SID96	A-CHNKS_D	Number of channels - differential	-	_	4		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	-	-	-		Yes
SID98	A_GAINERR	Gain error	-	_	±0.1	%	With external reference
SID99	A_OFFSET	Input offset voltage	-	_	2	mV	Measured with 1-V reference
SID100	A_ISAR	Current consumption	-	-	1	mA	
SID101	A_VINS	Input voltage range - single ended	V_{SS}	-	V _{DDA}	V	
SID102	A_VIND	Input voltage range - differential	V_{SS}	-	V _{DDA}	V	
SID103	A_INRES	Input resistance	_	-	2.2	KΩ	
SID104	A_INCAP	Input capacitance	_	-	10	pF	
SID260	VREFSAR	Trimmed internal reference to SAR	-	-	TBD	V	
SAR ADC	AC Specification	ons					
SID106	A_PSRR	Power supply rejection ratio	70	-	-	dB	
SID107	A_CMRR	Common mode rejection ratio	66	-	-	dB	Measured at 1 V
SID108	A_SAMP	Sample rate	-	-	1	Msps	
SID109	A_SNR	Signal-to-noise and distortion ratio (SINAD)	65	—	-	dB	F _{IN} = 10 kHz
SID110	A_BW	Input bandwidth without aliasing	-	-	A_samp/2	kHz	
SID111	A_INL	Integral non linearity. V _{DD} = 1.71 to 5.5, 1 Msps	-1.7	-	2	LSB	V_{REF} = 1 to V_{DD}
SID111A	A_INL	Integral non linearity. V _{DDD} = 1.71 to 3.6, 1 Msps	-1.5	-	1.7	LSB	V _{REF} = 1.71 to V _{DD}
SID111B	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	-1.5	-	1.7	LSB	V_{REF} = 1 to V_{DD}
SID112	A_DNL	Differential non linearity. V _{DD} = 1.71 to 5.5, 1 Msps	–1	-	2.2	LSB	V _{REF} = 1 to V _{DD}
SID112A	A_DNL	Differential non linearity. V _{DD} = 1.71 to 3.6, 1 Msps	-1	-	2	LSB	V _{REF} = 1.71 to V _{DD}
SID112B	A_DNL	Differential non linearity. V _{DD} = 1.71 to 5.5, 500 ksps	–1	-	2.2	LSB	V _{REF} = 1 to V _{DD}
SID113	A_THD	Total harmonic distortion	-	—	-65	dB	Fin = 10 kHz
SID261	FSARINTREF	SAR operating speed without external reference bypass	I	_	100	ksps	12-bit resolution



CSD and IDAC

Table 13. CSD and IDAC Specifications

SPEC ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SYS.PER#3	VDD_RIPPLE	Max allowed ripple on power supply, DC to 10 MHz	-	-	±50	mV	V _{DD} > 2 V (with ripple), 25 °C T _A , Sensitivity = 0.1 pF
SYS.PER#16	VDD_RIPPLE_1.8	Max allowed ripple on power supply, DC to 10 MHz	-	_	±25	mV	V_{DD} > 1.75V (with ripple), 25 °C T _A , Parasitic Capaci- tance (C _P) < 20 pF, Sensitivity ≥ 0.4 pF
SID.CSD.BLK	ICSD	Maximum block current	_	_	4000	μA	Maximum block current for both IDACs in dynamic (switching) mode including comparators, buffer, and reference generator
SID.CSD#15	V _{REF}	Voltage reference for CSD and Comparator	0.6	1.2	V _{DDA} - 0.6	V	V _{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#15A	VREF_EXT	External Voltage reference for CSD and Comparator	0.6		V _{DDA} - 0.6	V	V _{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#16	IDAC1IDD	IDAC1 (7-bits) block current	-	-	1750	μA	
SID.CSD#17	IDAC2IDD	IDAC2 (7-bits) block current	-	-	1750	μA	
SID308	VCSD	Voltage range of operation	1.71	-	5.5	V	1.8 V ±5% or 1.8 V to 5.5 V
SID308A	VCOMPIDAC	Voltage compliance range of IDAC	0.6	-	V _{DDA} –0.6	V	V _{DDA} - 0.06 or 4.4, whichever is lower
SID309	IDAC1DNL	DNL	-1	-	1	LSB	
SID310	IDAC1INL	INL	-2	-	2	LSB	INL is ±5.5 LSB for V _{DDA} < 2 V
SID311	IDAC2DNL	DNL	-1	-	1	LSB	
SID312	IDAC2INL	INL	-2	_	2	LSB	INL is ±5.5 LSB for V _{DDA} < 2 V
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	-	-	Ratio	Capacitance range of 5 to 35 pF, 0.1-pF sensitivity. All use cases. V _{DDA} > 2 V.
SID314	IDAC1CRT1	Output current of IDAC1 (7 bits) in low range	4.2	-	5.4	μA	LSB = 37.5-nA typ
SID314A	IDAC1CRT2	Output current of IDAC1(7 bits) in medium range	34	-	41	μA	LSB = 300-nA typ
SID314B	IDAC1CRT3	Output current of IDAC1(7 bits) in high range	275	-	330	μA	LSB = 2.4-µA typ
SID314C	IDAC1CRT12	Output current of IDAC1 (7 bits) in low range, 2X mode	8	-	10.5	μA	LSB = 75-nA typ
SID314D	IDAC1CRT22	Output current of IDAC1(7 bits) in medium range, 2X mode	69	-	82	μA	LSB = 600-nA typ.
SID314E	IDAC1CRT32	Output current of IDAC1(7 bits) in high range, 2X mode	540	-	660	μA	LSB = 4.8-µA typ
SID315	IDAC2CRT1	Output current of IDAC2 (7 bits) in low range	4.2	-	5.4	μA	LSB = 37.5-nA typ
SID315A	IDAC2CRT2	Output current of IDAC2 (7 bits) in medium range	34	-	41	μA	LSB = 300-nA typ
SID315B	IDAC2CRT3	Output current of IDAC2 (7 bits) in high range	275	-	330	μA	LSB = 2.4-µA typ
SID315C	IDAC2CRT12	Output current of IDAC2 (7 bits) in low range, 2X mode	8	-	10.5	μA	LSB = 75-nA typ
SID315D	IDAC2CRT22	Output current of IDAC2(7 bits) in medium range, 2X mode	69	-	82	μA	LSB = 600-nA typ
SID315E	IDAC2CRT32	Output current of IDAC2(7 bits) in high range, 2X mode	540	-	660	μA	LSB = 4.8-µA typ
SID315F	IDAC3CRT13	Output current of IDAC in 8-bit mode in low range	8	-	10.5	μA	LSB = 37.5-nA typ



Table 13.	CSD and	IDAC Specifications	(continued)
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SPEC ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID315G	IDAC3CRT23	Output current of IDAC in 8-bit mode in medium range	69	-	82	μA	LSB = 300-nA typ
SID315H	IDAC3CRT33	Output current of IDAC in 8-bit mode in high range	540	-	660	μA	LSB = 2.4-µA typ
SID320	IDACOFFSET	All zeroes input	-	_	1	LSB	Polarity set by Source or Sink. Offset is 2 LSBs for 37.5 nA/LSB mode
SID321	IDACGAIN	Full-scale error less offset	_	-	±10	%	
SID322	IDACMISMATCH1	Mismatch between IDAC1 and IDAC2 in Low mode	_	-	9.2	LSB	LSB = 37.5-nA typ
SID322A	IDACMISMATCH2	Mismatch between IDAC1 and IDAC2 in Medium mode	-	-	5.6	LSB	LSB = 300-nA typ
SID322B	IDACMISMATCH3	Mismatch between IDAC1 and IDAC2 in High mode	_	-	6.8	LSB	LSB = 2.4-µA typ
SID323	IDACSET8	Settling time to 0.5 LSB for 8-bit IDAC	_	-	5	μs	Full-scale transition. No external load
SID324	IDACSET7	Settling time to 0.5 LSB for 7-bit IDAC	_	_	5	μs	Full-scale transition. No external load
SID325	CMOD	External modulator capacitor.	_	2.2	-	nF	5-V rating, X7R or NP0 cap

10-bit CapSense ADC

Table 14. 10-bit CapSense ADC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SIDA94	A_RES	Resolution	-	-	10	bits	Auto-zeroing is required every millisecond
SIDA95	A_CHNLS_S	Number of channels - single ended	-	-	16		Defined by AMUX Bus
SIDA97	A-MONO	Monotonicity	-	-	-	Yes	
SIDA98	A_GAINERR	Gain error	-	-	±3	%	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 μ F
SIDA99	A_OFFSET	Input offset voltage	_	_	±18	mV	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 μ F
SIDA100	A_ISAR	Current consumption	-	-	0.25	mA	
SIDA101	A_VINS	Input voltage range - single ended	V _{SSA}	-	V _{DDA}	V	
SIDA103	A_INRES	Input resistance	_	2.2	-	KΩ	
SIDA104	A_INCAP	Input capacitance	_	20	-	pF	
SIDA106	A_PSRR	Power supply rejection ratio	-	60	_	dB	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 μ F
SIDA107	A_TACQ	Sample acquisition time	-	1	-	μs	
SIDA108	A_CONV8	Conversion time for 8-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	_	-	21.3	μs	Does not include acqui- sition time. Equivalent to 44.8 ksps including acquisition time.
SIDA108A	A_CONV10	Conversion time for 10-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	_	_	85.3	μs	Does not include acqui- sition time. Equivalent to 11.6 ksps including acquisition time.



Table 14. 10-bit CapSense ADC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SIDA109	A_SND	Signal-to-noise and Distortion ratio (SINAD)	-	61	-		With 10-Hz input sine wave, external 2.4-V reference, V _{REF} (2.4 V) mode
SIDA110	A_BW	Input bandwidth without aliasing	_	-	22.4	KHz	8-bit resolution
SIDA111	A_INL	Integral Non Linearity. 1 ksps	-	-	2	LSB	V _{REF} = 2.4 V or greater
SIDA112	A_DNL	Differential Non Linearity. 1 ksps	-	—	1	LSB	

Digital Peripherals

Timer Counter Pulse-Width Modulator (TCPWM)

Table 15. TCPWM Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID.TCPWM.1	ITCPWM1	Block current consumption at 3 MHz	-	-	45		All modes (TCPWM)
SID.TCPWM.2	ITCPWM2	Block current consumption at 12 MHz	-	-	155	μA	All modes (TCPWM)
SID.TCPWM.2A	ITCPWM3	Block current consumption at 48 MHz	-	-	650		All modes (TCPWM)
SID.TCPWM.3	TCPWM _{FREQ}	Operating frequency	_	-	Fc	MHz	Fc max = CLK_SYS Maximum = 48 MHz
SID.TCPWM.4	TPWM _{ENEXT}	Input trigger pulse width	2/Fc	-	-		For all trigger events ^[7]
SID.TCPWM.5	TPWM _{EXT}	Output trigger pulse widths	2/Fc	-	_		Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) outputs
SID.TCPWM.5A	TC _{RES}	Resolution of counter	1/Fc	-	_	ns	Minimum time between successive counts
SID.TCPWM.5B	PWM _{RES}	PWM resolution	1/Fc	-	_		Minimum pulse width of PWM Output
SID.TCPWM.5C	Q _{RES}	Quadrature inputs resolution	1/Fc	_	_		Minimum pulse width between Quadrature phase inputs

ľC

Table 16. Fixed I²C DC Specifications^[7]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID149	I _{I2C1}	Block current consumption at 100 kHz	-	-	50		_
SID150	I _{I2C2}	Block current consumption at 400 kHz	-	-	135		_
SID151	I _{I2C3}	Block current consumption at 1 Mbps	-	-	310	μA	_
SID152	I _{I2C4}	I ² C enabled in Deep Sleep mode	-	1	-		

Table 17. Fixed I²C AC Specifications^[7]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID153	F _{I2C1}	Bit rate	-	-	1	Msps	-

Note 7. Guaranteed by characterization.



SPI

Table 18. SPI DC Specifications^[8]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID163	ISPI1	Block current consumption at 1 Mbps	-	-	360	μA	-
SID164	ISPI2	Block current consumption at 4 Mbps	-	-	560		-
SID165	ISPI3	Block current consumption at 8 Mbps	-	-	600		-

Table 19. SPI AC Specifications^[8]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID166	FSPI	SPI Operating frequency (Master; 6X Oversampling)	-	-	8	MHz	
Fixed SPI	Master Mode A	C Specifications					
SID167	TDMO	MOSI Valid after SClock driving edge	-	-	15		_
SID168	TDSI	MISO Valid before SClock capturing edge	20	-	-	ns	Full clock, late MISO sampling
SID169	тнмо	Previous MOSI data hold time	0	-	_		Referred to Slave capturing edge
Fixed SPI	Slave Mode AC	Specifications			-		
SID170	томі	MOSI Valid before Sclock Capturing edge	40	-	-		-
SID171	TDSO	MISO Valid after Sclock driving edge	-	-	42 + 3*Tcpu	ns	T _{CPU} = 1/F _{CPU}
SID171A	TDSO_EXT	MISO Valid after Sclock driving edge in Ext. Clk mode	_	-	48		_
SID172	THSO	Previous MISO data hold time	0	_	-		_
SID172A	TSSELSSCK	SSEL Valid to first SCK Valid edge	-	-	100	ns	-

UART

Table 20. UART DC Specifications^[8]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID160	I _{UART1}	Block current consumption at 100 Kbps	-	-	55	μA	_
SID161	I _{UART2}	Block current consumption at 1000 Kbps	-	-	312	μA	-

Table 21. UART AC Specifications^[8]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID162	F _{UART}	Bit rate	-	1	1	Mbps	_



LCD Direct Drive

Table 22. LCD Direct Drive DC Specifications^[9]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID154	ILCDLOW	Operating current in low power mode	-	5	-	μA	16 \times 4 small segment disp. at 50 Hz
SID155	C _{LCDCAP}	LCD capacitance per segment/common driver	_	500	5000	pF	-
SID156	LCD _{OFFSET}	Long-term segment offset	-	20	-	mV	-
SID157	I _{LCDOP1}	LCD system operating current Vbias = 5 V	_	2	-	mA	32 × 4 segments at 50 Hz 25 °C
SID158	I _{LCDOP2}	LCD system operating current Vbias = 3.3 V	_	2	Ι	ШĄ	32 × 4 segments at 50 Hz 25 °C

Table 23. LCD Direct Drive AC Specifications^[9]

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID159	F _{LCD}	LCD frame rate	10	50	150	Hz	-



SWD Interface

Table 28. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID213	F_SWDCLK1	$3.3~V \leq V_{DD} \leq 5.5~V$	-	Ι	14	- MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	$1.71 \text{ V} \leq \text{V}_{DD} \leq 3.3 \text{ V}$	-	-	7		SWDCLK ≤ 1/3 CPU clock frequency
SID215 ^[12]	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	-	_		-
SID216 ^[12]	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	-	_	ne	-
SID217 ^[12]	T_SWDO_VALID	T = 1/f SWDCLK	-	-	0.5*T	ns	-
SID217A ^[12]	T_SWDO_HOLD	T = 1/f SWDCLK	1	-	—		_

Internal Main Oscillator

Table 29. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID218	I _{IMO1}	IMO operating current at 48 MHz	-	-	250	μA	-
SID219	I _{IMO2}	IMO operating current at 24 MHz	-	-	180	μA	_

Table 30. IMO AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID223	F _{IMOTOL1}	Frequency variation at 24, 32, and 48 MHz (trimmed)	_	-	±2	%	
SID226	T _{STARTIMO}	IMO startup time	-	-	7	μs	_
SID228	T _{JITRMSIMO2}	RMS jitter at 24 MHz	_	145	-	ps	_

Internal Low-Speed Oscillator

Table 31. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID231	I _{ILO1}	ILO operating current		0.3	1.05	μA	_

Table 32. ILO AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID234 ^[12]	T _{STARTILO1}	ILO startup time	-	-	2	ms	-
SID236 ^[12]	T _{ILODUTY}	ILO duty cycle	40	50	60	%	-
SID237	F _{ILOTRIM1}	ILO frequency range	20	40	80	kHz	_



Figure 8. 64-pin TQFP Package (0.5-mm Pitch) Outline

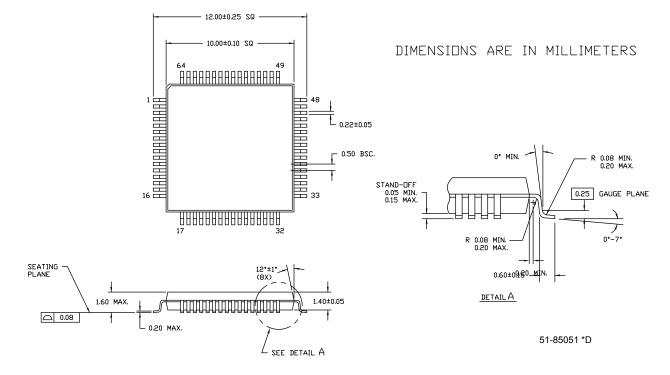
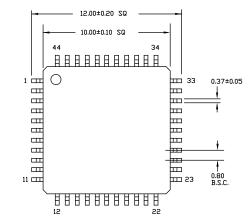
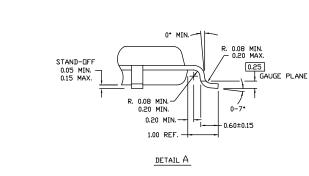
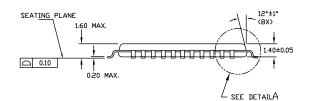


Figure 9. 44-Pin TQFP Package Outline







NDTE:

- 1. JEDEC STD REF MS-026
- BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
 DIMENSIONS IN MILLIMETERS

51-85064 *G



Document Conventions

Units of Measure

Table 45. Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
dB	decibel
fF	femto farad
Hz	hertz
KB	1024 bytes
kbps	kilobits per second
Khr	kilohour
kHz	kilohertz
kΩ	kilo ohm
ksps	kilosamples per second
LSB	least significant bit
Mbps	megabits per second
MHz	megahertz
MΩ	mega-ohm
Msps	megasamples per second
μA	microampere
μF	microfarad
μH	microhenry
μs	microsecond
μV	microvolt
μW	microwatt
mA	milliampere
ms	millisecond
mV	millivolt
nA	nanoampere
ns	nanosecond
nV	nanovolt
Ω	ohm
pF	picofarad
ppm	parts per million
ps	picosecond
S	second
sps	samples per second
sqrtHz	square root of hertz
V	volt



Revision History

Description Title: PSoC [®] 4: PSoC 4100S Plus Datasheet Programmable System-on-Chip (PSoC) Document Number: 002-19966				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
*E	5995731	WKA	12/15/2017	New release
*F	6069640	JIAO	02/13/2018	Updated Pinouts and DC Specifications.
*G	6169676	WKA	05/09/2018	Updated Clock Diagram to show Watchdog details and clock divider infor- mation. Removed preliminary statement in Pinouts.